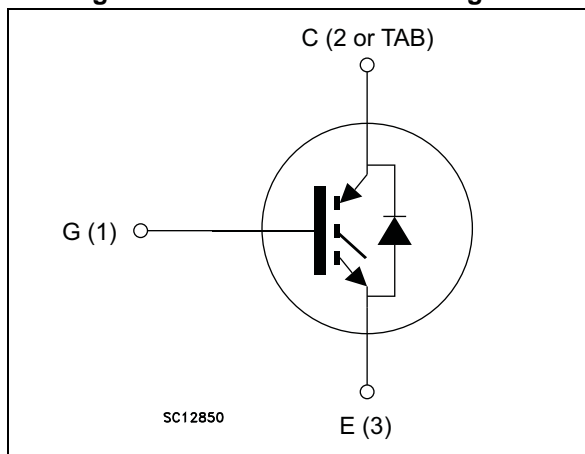


Figure 1. Internal schematic diagram



### Features

- Maximum junction temperature:  $T_J = 175\text{ °C}$
- High speed switching series
- Minimized tail current
- Low saturation voltage:  $V_{CE(sat)} = 1.6\text{ V (typ.)}$   
@  $I_C = 40\text{ A}$
- Tight parameters distribution
- Safe paralleling
- Low thermal resistance
- Low  $V_F$  soft recovery co-packaged diode
- Lead free package

### Applications

- Induction heating
- Microwave oven
- Resonant converters

### Description

This device is an IGBT developed using an advanced proprietary trench gate field stop structure. The device is part of the new HB series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of any frequency converter. Furthermore, a slightly positive  $V_{CE(sat)}$  temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Table 1. Device summary

Order code	Marking	Package	Packaging
STGW40H60DLFB	GW40H60DLFB	TO-247	Tube
STGWT40H60DLFB	GWT40H60DLFB	TO-3P	Tube

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
	2.1 Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>11</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>12</b>
	4.1 TO-247, STGW40H60DLFB .....	12
	4.2 TO-3P, STGWT40H60DLFB .....	14
<b>5</b>	<b>Revision history</b> .....	<b>16</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ )	600	V
$I_C$	Continuous collector current at $T_C = 25\text{ °C}$	80	A
$I_C$	Continuous collector current at $T_C = 100\text{ °C}$	40	A
$I_{CP}^{(1)}$	Pulsed collector current	160	A
$V_{GE}$	Gate-emitter voltage	$\pm 20$	V
$I_F$	Continuous forward current at $T_C = 25\text{ °C}$	80	A
$I_F$	Continuous forward current at $T_C = 100\text{ °C}$	40	A
$I_{FP}^{(1)}$	Pulsed forward current	160	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	283	W
$T_{STG}$	Storage temperature range	- 55 to 150	°C
$T_J$	Operating junction temperature	- 55 to 175	°C

1. Pulse width limited by maximum junction temperature

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance junction-case IGBT	0.53	°C/W
$R_{thJC}$	Thermal resistance junction-case diode	1.47	°C/W
$R_{thJA}$	Thermal resistance junction-ambient	50	°C/W

## 2 Electrical characteristics

$T_J = 25\text{ °C}$  unless otherwise specified.

**Table 4. Static characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage ( $V_{GE} = 0$ )	$I_C = 2\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$		1.6	2	V
		$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ $T_J = 125\text{ °C}$		1.7		
		$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ $T_J = 175\text{ °C}$		1.8		
$V_F$	Forward on-voltage	$I_F = 40\text{ A}$		1.55	1.8	V
		$I_F = 40\text{ A}, T_J = 125\text{ °C}$		1.3		
		$I_F = 40\text{ A}, T_J = 175\text{ °C}$		1.25		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$	5	6	7	V
$I_{CES}$	Collector cut-off current ( $V_{GE} = 0$ )	$V_{CE} = 600\text{ V}$			25	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current ( $V_{CE} = 0$ )	$V_{GE} = \pm 20\text{ V}$			250	nA

**Table 5. Dynamic characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GE} = 0$	-	5412	-	pF
$C_{oes}$	Output capacitance		-	198	-	pF
$C_{res}$	Reverse transfer capacitance		-	107	-	pF
$Q_g$	Total gate charge	$V_{CC} = 480\text{ V}, I_C = 40\text{ A},$ $V_{GE} = 15\text{ V},$ see <a href="#">Figure 27</a>	-	210	-	nC
$Q_{ge}$	Gate-emitter charge		-	39	-	nC
$Q_{gc}$	Gate-collector charge		-	82	-	nC

Table 6. IGBT switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off delay time	$V_{CE} = 400\text{ V}$ , $I_C = 40\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , see <a href="#">Figure 25</a>		142		ns
$t_f$	Current fall time		-	27.6	-	ns
$E_{off}^{(1)}$	Turn-off switching losses		-	363	-	$\mu\text{J}$
$t_{d(off)}$	Turn-off delay time	$V_{CE} = 400\text{ V}$ , $I_C = 40\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$ , see <a href="#">Figure 25</a>		141		ns
$t_f$	Current fall time		-	61	-	ns
$E_{off}^{(1)}$	Turn-off switching losses		-	764	-	$\mu\text{J}$

1. Turn-off losses include also the tail of the collector current.

Table 7. IGBT switching characteristics (capacitive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{off}^{(1)}$	Turn-off switching losses	$V_{CC} = 320\text{ V}$ , $R_G = 10\ \Omega$ , $I_C = 40\text{ A}$ , $L = 100\ \mu\text{H}$ , $C_{snub} = 20\text{ nF}$ , see <a href="#">Figure 26</a>	-	190	-	$\mu\text{J}$
		$V_{CC} = 320\text{ V}$ , $R_G = 10\ \Omega$ , $I_C = 40\text{ A}$ , $L = 100\ \mu\text{H}$ , $C_{snub} = 20\text{ nF}$ , $T_J = 175\text{ }^\circ\text{C}$ , see <a href="#">Figure 26</a>	-	290	-	

1. Turn-off losses include also the tail of the collector current.

## 2.1 Electrical characteristics (curves)

Figure 2. Power dissipation vs. case temperature

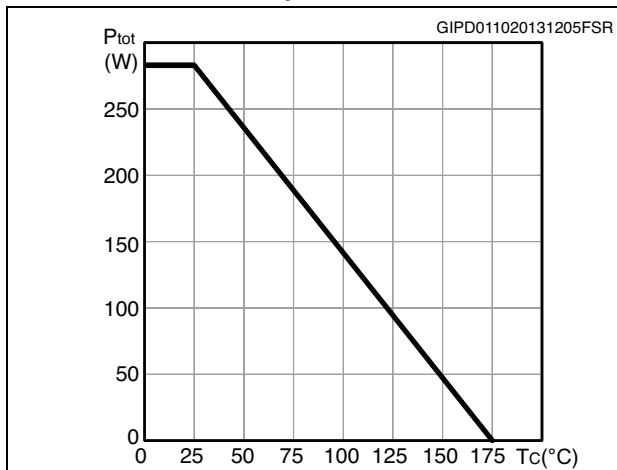


Figure 3. Collector current vs. case temperature

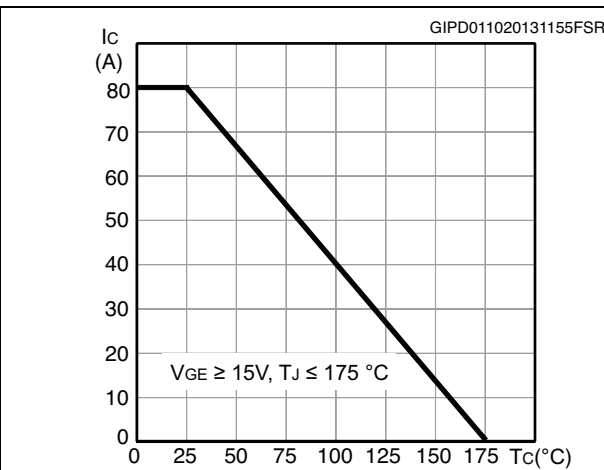


Figure 4. Output characteristics (T<sub>J</sub> = 25°C)

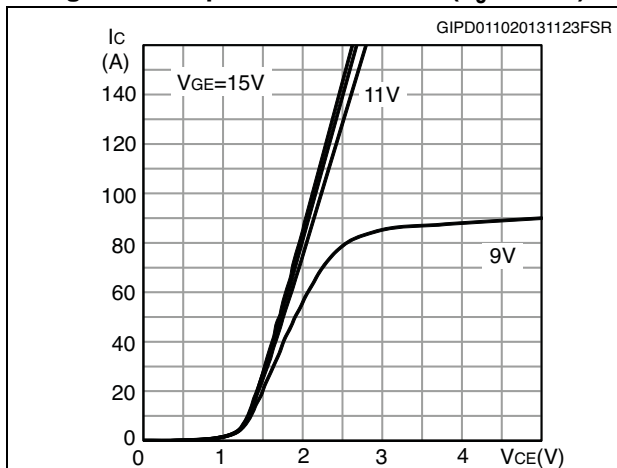


Figure 5. Output characteristics (T<sub>J</sub> = 175°C)

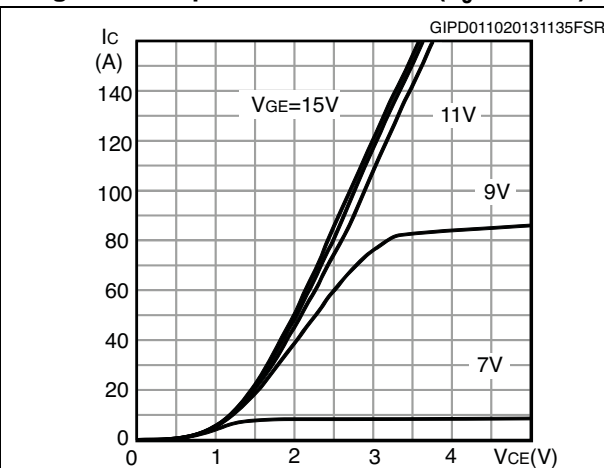


Figure 6. V<sub>CE(sat)</sub> vs. junction temperature

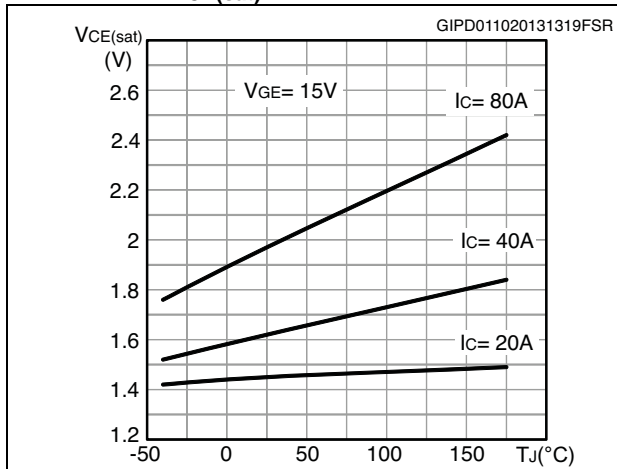


Figure 7. V<sub>CE(sat)</sub> vs. collector current

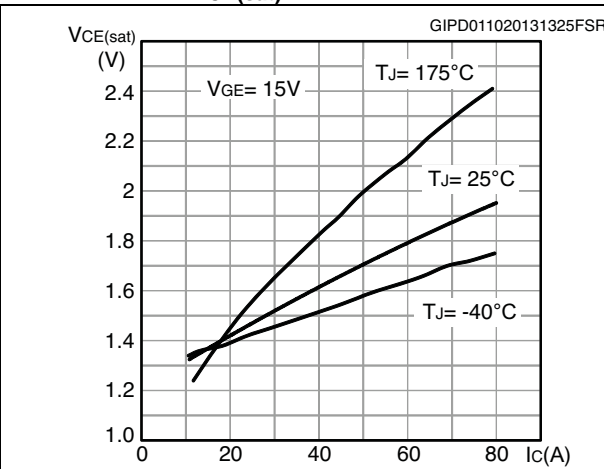


Figure 8. Collector current vs. switching frequency

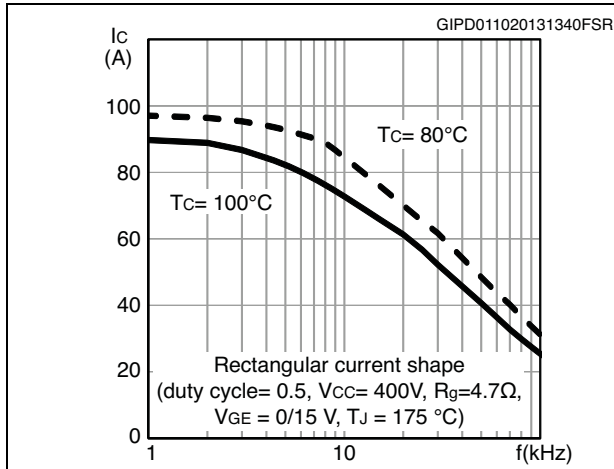


Figure 9. Forward bias safe operating area

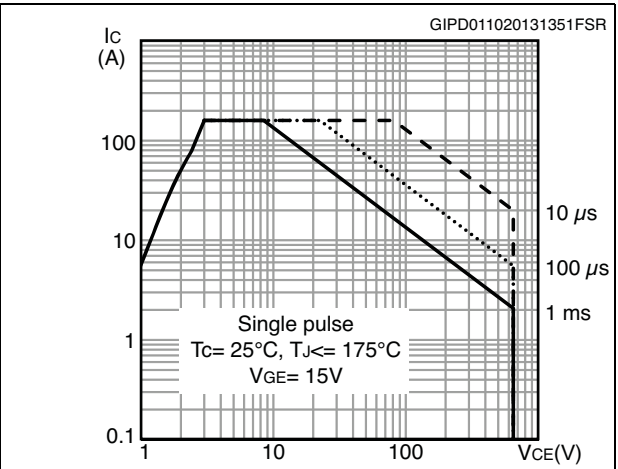


Figure 10. Transfer characteristics

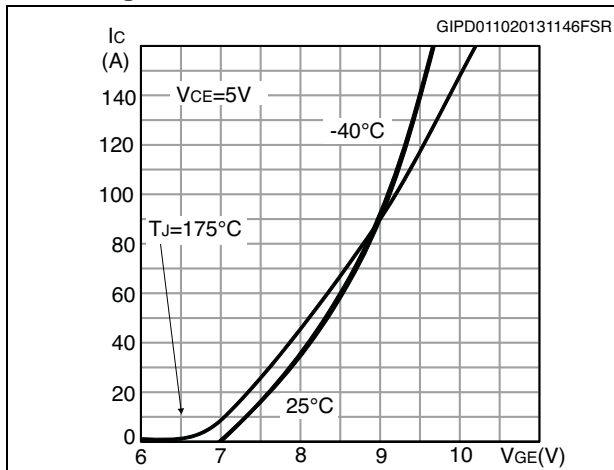


Figure 11. Diode VF vs. forward current

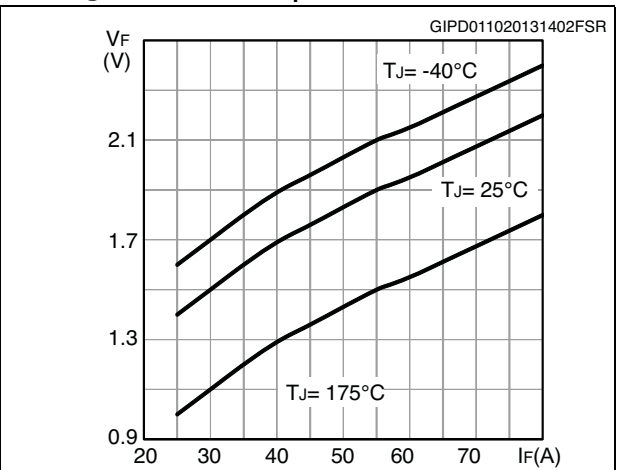


Figure 12. Normalized VGE(th) vs junction temperature

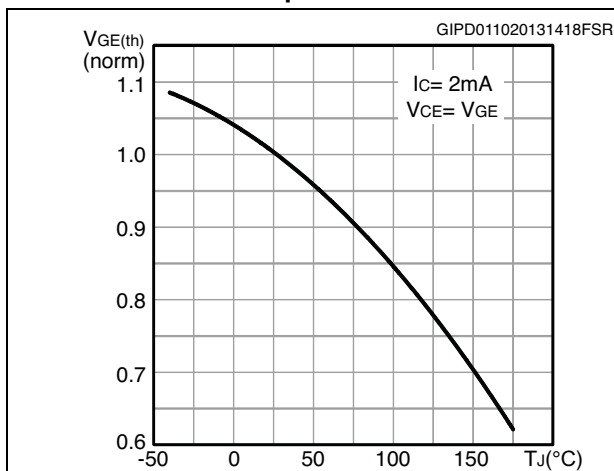


Figure 13. Normalized V(BR)CES vs. junction temperature

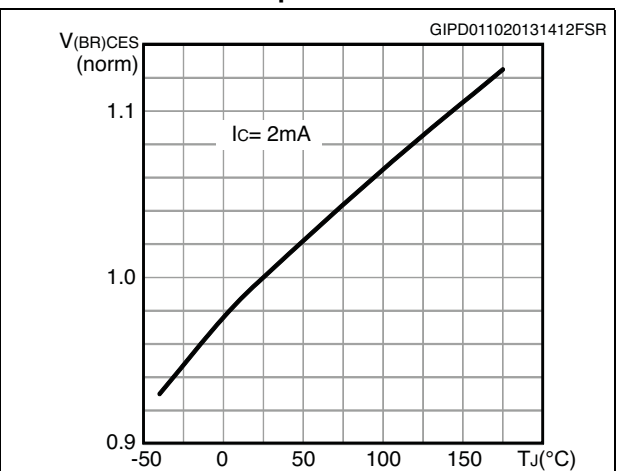


Figure 14. Capacitance variation

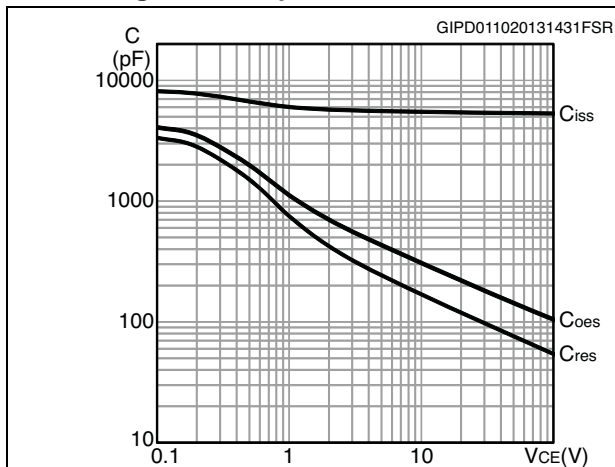


Figure 15. Gate charge vs. gate-emitter voltage

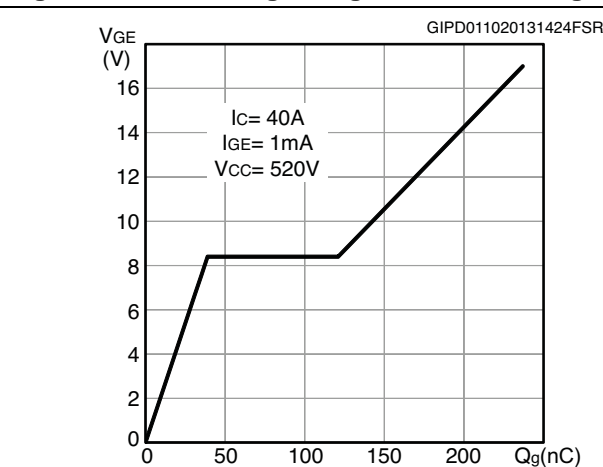


Figure 16. Switching-off loss vs collector current

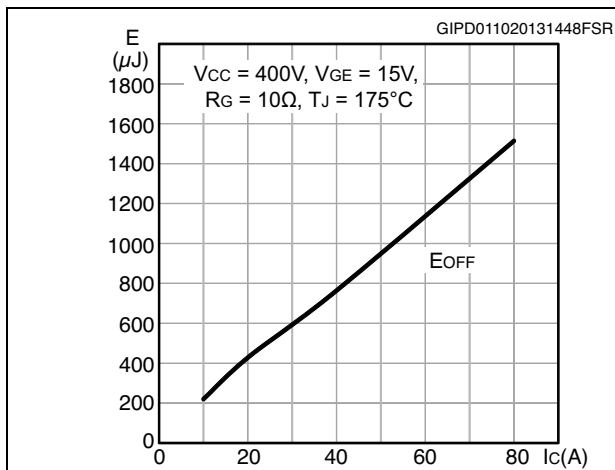


Figure 17. Switching-off loss vs gate resistance

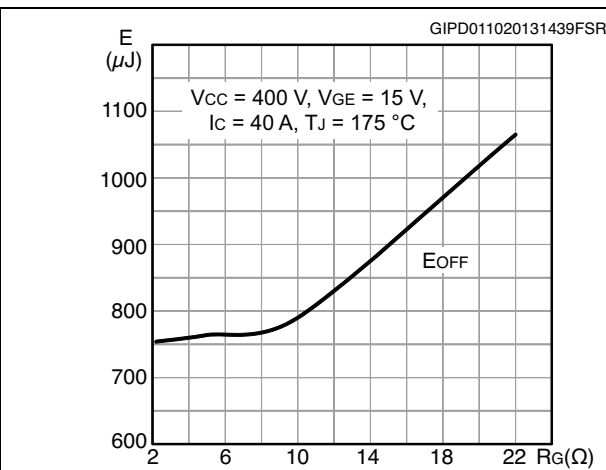


Figure 18. Switching-off loss vs temperature

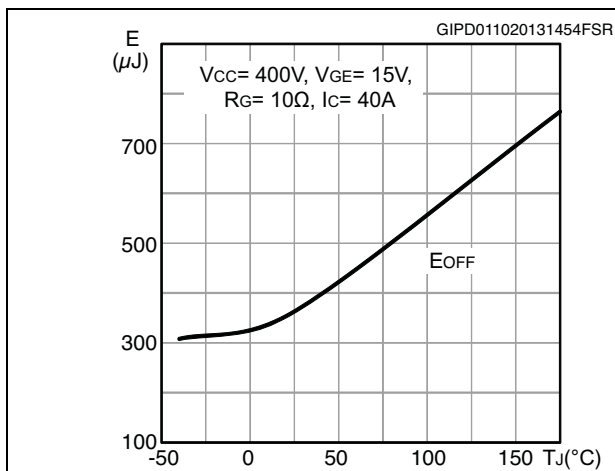


Figure 19. Switching-off loss vs collector-emitter voltage

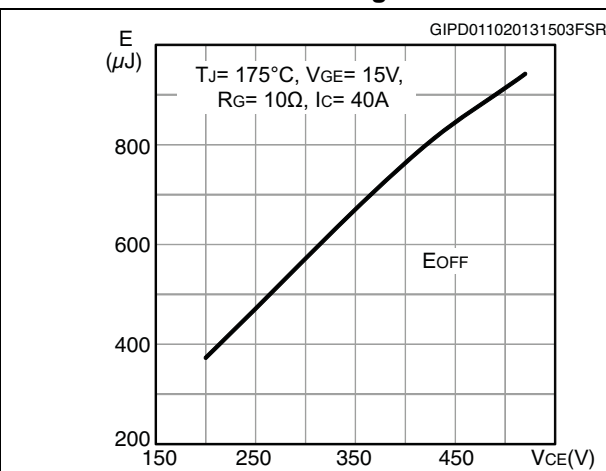




Figure 20. Switching times vs. collector current    Figure 21. Switching times vs. gate resistance

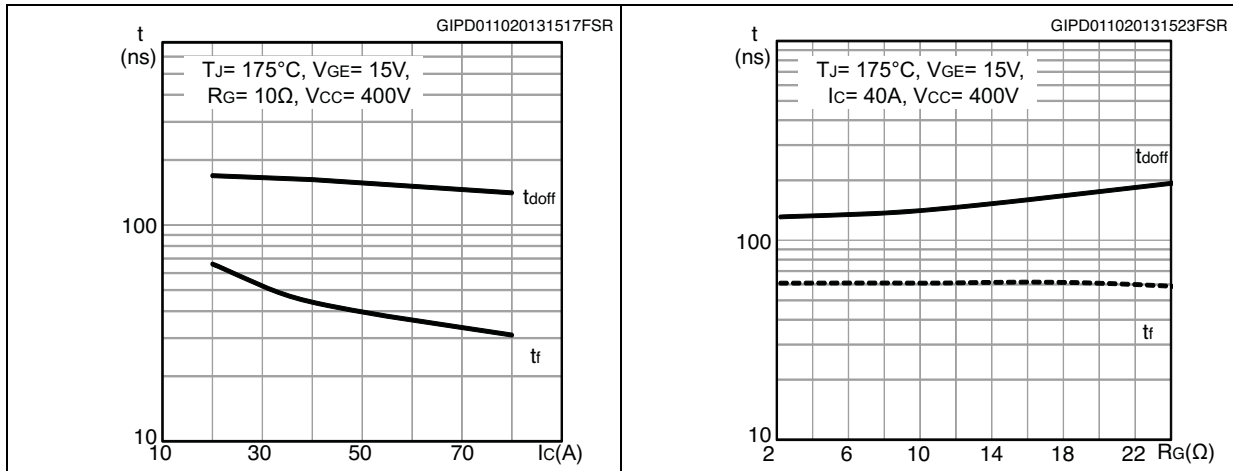


Figure 22. Switching-off losses vs. capacitive load

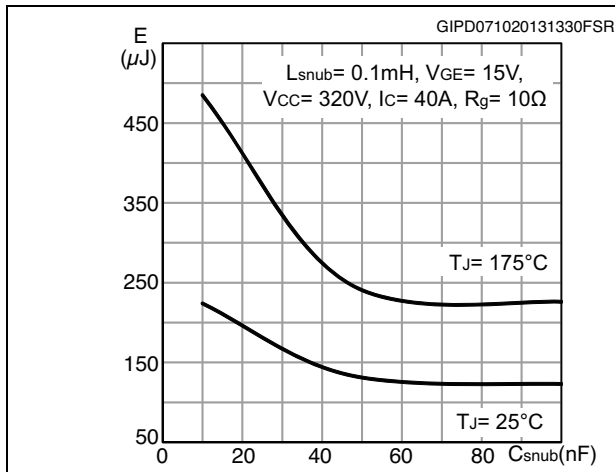


Figure 23. Thermal impedance for IGBT

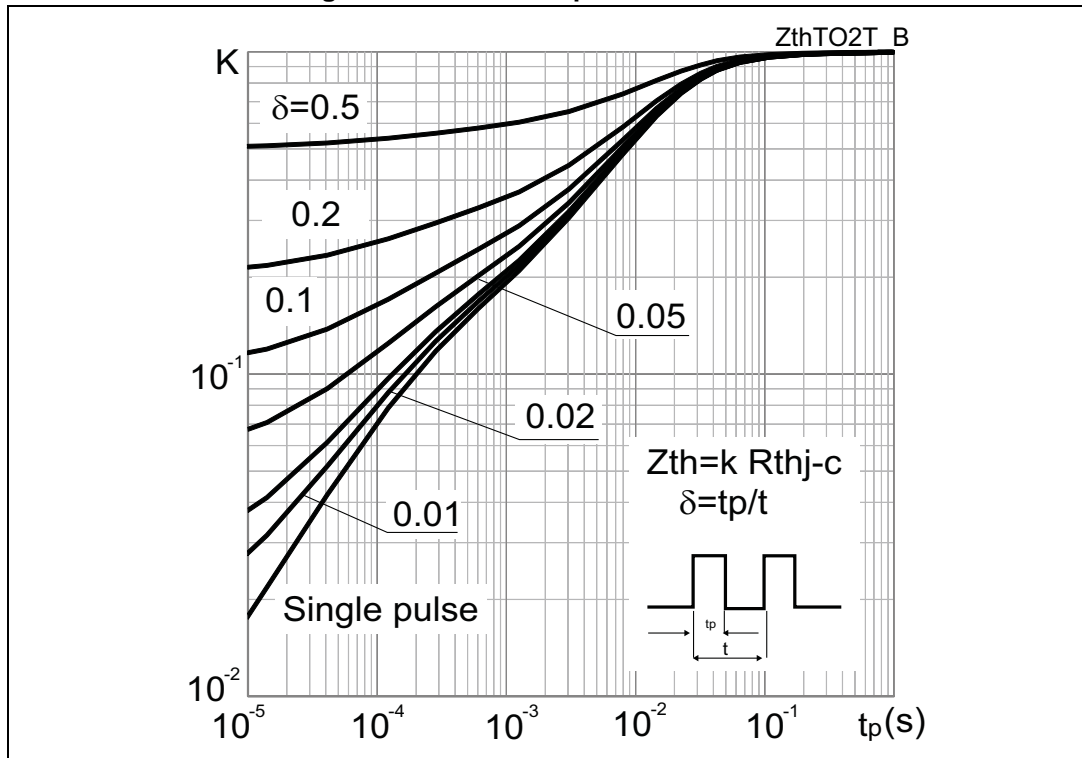
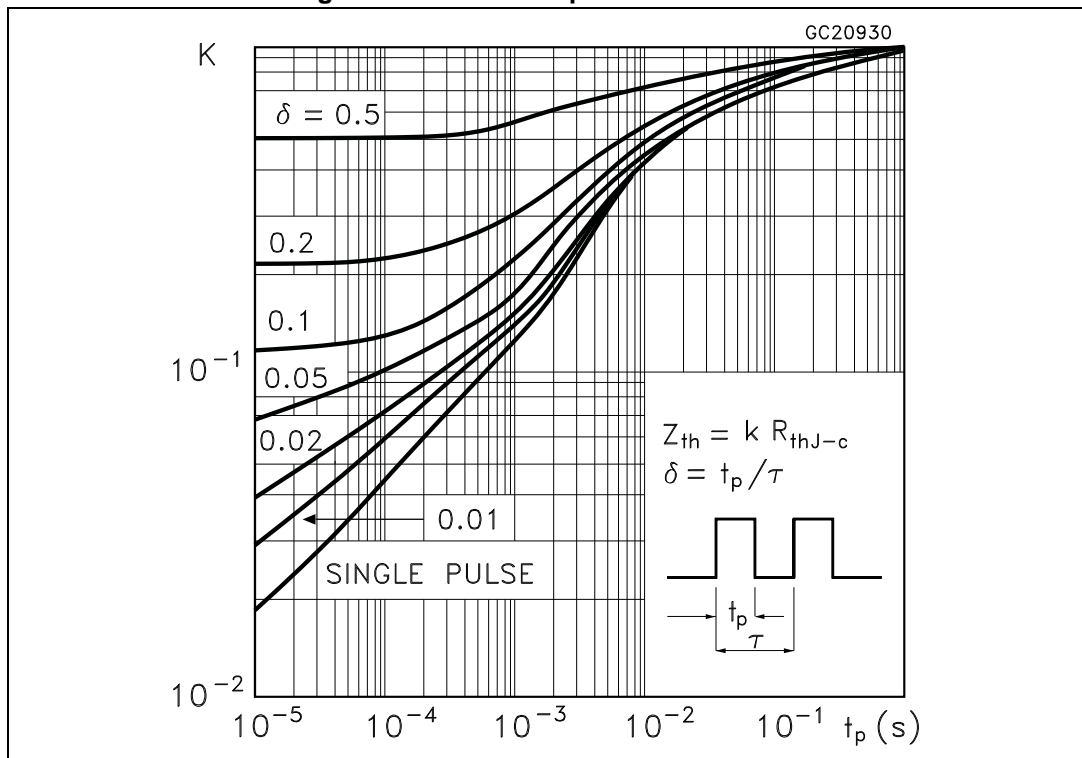


Figure 24. Thermal impedance for diode



### 3 Test circuits

Figure 25. Test circuit for inductive load switching



Figure 26. Test circuit for capacitive load switching

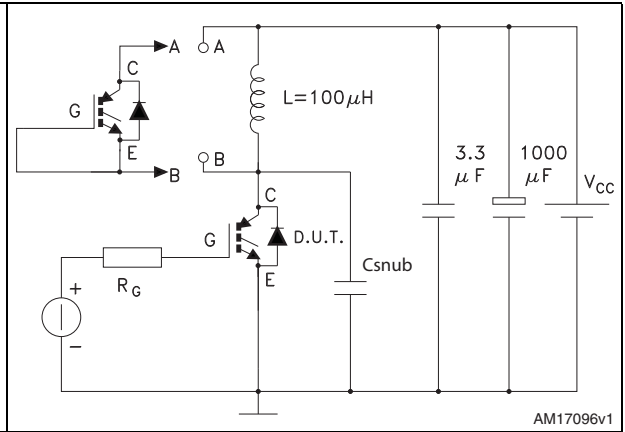


Figure 27. Gate charge test circuit



Figure 28. Switching waveform

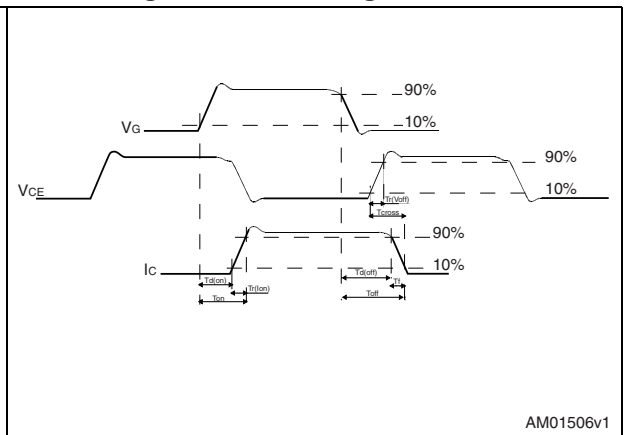
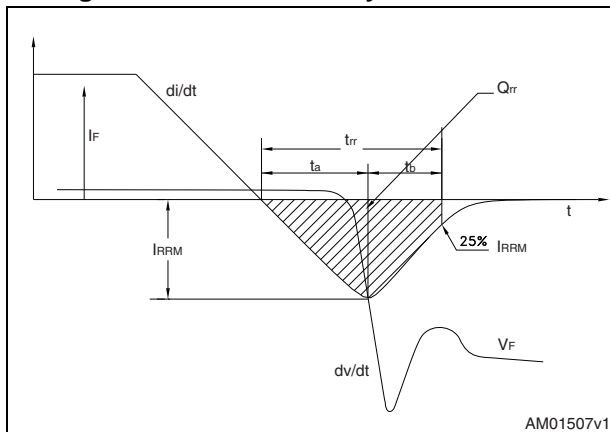


Figure 29. Diode recovery time waveform



## 4 Package mechanical data

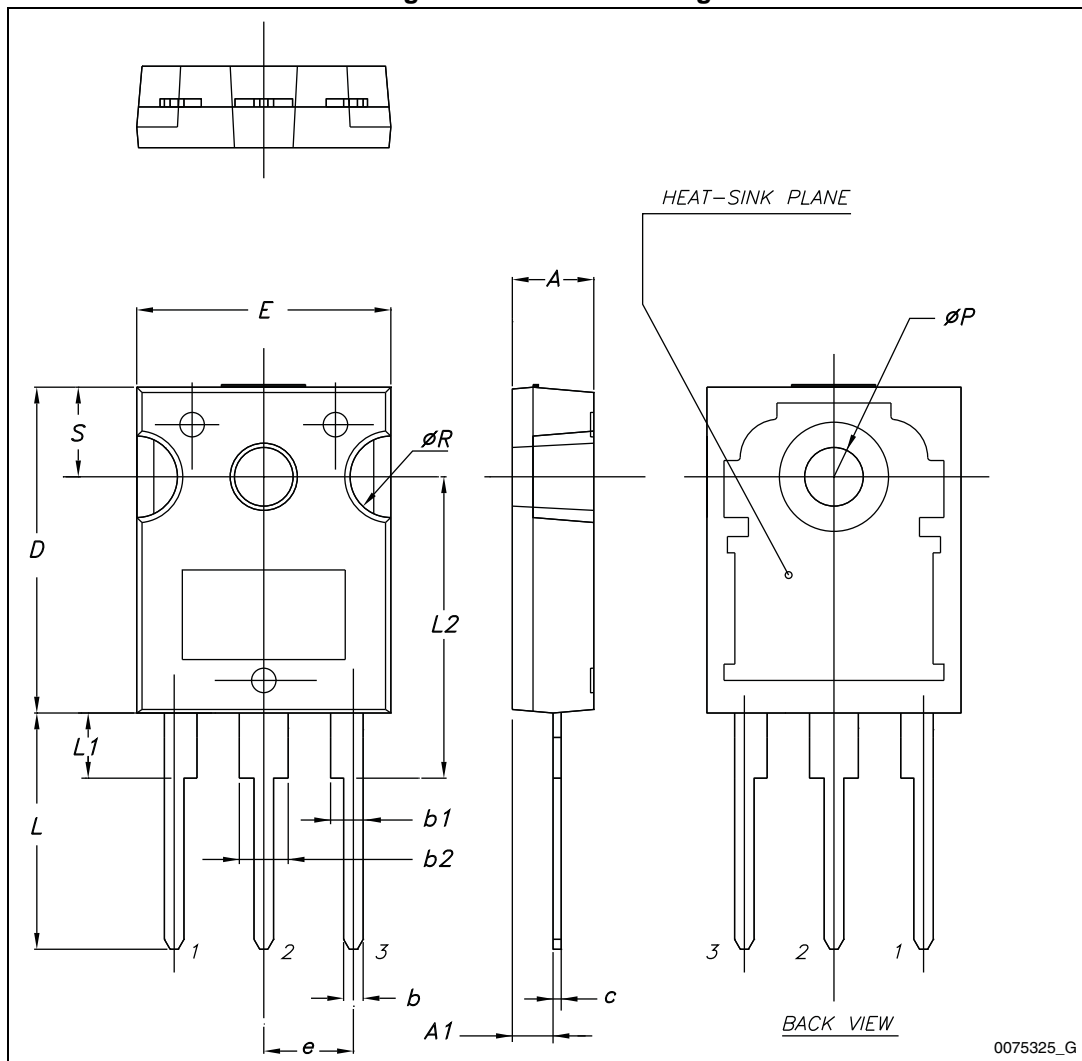
In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 TO-247, STGW40H60DLFB

Table 8. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 30. TO-247 drawing

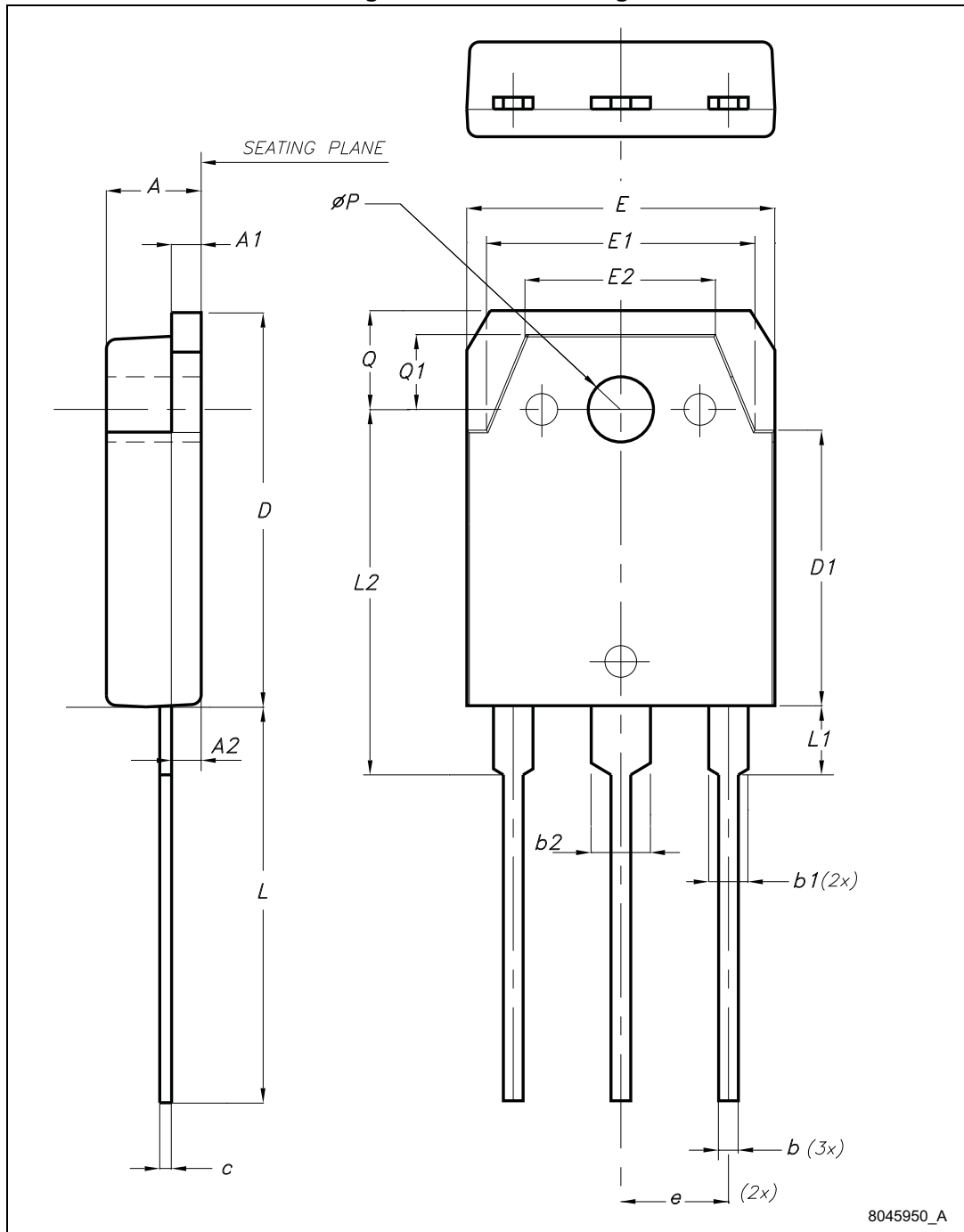


## 4.2 TO-3P, STGWT40H60DLFB

Table 9. TO-3P mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.60		5
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1	1.20
b1	1.80		2.20
b2	2.80		3.20
c	0.55	0.60	0.75
D	19.70	19.90	20.10
D1		13.90	
E	15.40		15.80
E1		13.60	
E2		9.60	
e	5.15	5.45	5.75
L	19.50	20	20.50
L1		3.50	
L2	18.20	18.40	18.60
øP	3.10		3.30
Q		5	
Q1		3.80	

Figure 31. TO-3P drawing



8045950\_A

## 5 Revision history

Table 10. Document revision history

Date	Revision	Changes
12-Mar-2013	1	Initial release.
07-Oct-2013	2	Document status changed from preliminary to production data. Added <a href="#">Section 2.1: Electrical characteristics (curves)</a> . Minor text changes.
13-Mar-2014	3	Updated title and description in cover page.
18-Mar-2014	4	Updated title in cover page and <a href="#">Section 4: Package mechanical data</a> .



**Please Read Carefully:**

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

**UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.**

**ST PRODUCTS ARE NOT DESIGNED OR AUTHORIZED FOR USE IN: (A) SAFETY CRITICAL APPLICATIONS SUCH AS LIFE SUPPORTING, ACTIVE IMPLANTED DEVICES OR SYSTEMS WITH PRODUCT FUNCTIONAL SAFETY REQUIREMENTS; (B) AERONAUTIC APPLICATIONS; (C) AUTOMOTIVE APPLICATIONS OR ENVIRONMENTS, AND/OR (D) AEROSPACE APPLICATIONS OR ENVIRONMENTS. WHERE ST PRODUCTS ARE NOT DESIGNED FOR SUCH USE, THE PURCHASER SHALL USE PRODUCTS AT PURCHASER'S SOLE RISK, EVEN IF ST HAS BEEN INFORMED IN WRITING OF SUCH USAGE, UNLESS A PRODUCT IS EXPRESSLY DESIGNATED BY ST AS BEING INTENDED FOR "AUTOMOTIVE, AUTOMOTIVE SAFETY OR MEDICAL" INDUSTRY DOMAINS ACCORDING TO ST PRODUCT DESIGN SPECIFICATIONS. PRODUCTS FORMALLY ESCC, QML OR JAN QUALIFIED ARE DEEMED SUITABLE FOR USE IN AEROSPACE BY THE CORRESPONDING GOVERNMENTAL AGENCY.**

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2014 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

[www.st.com](http://www.st.com)